PowerMOS transistor — BUK416-100AE/BE

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in ISOTOP envelope.
The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

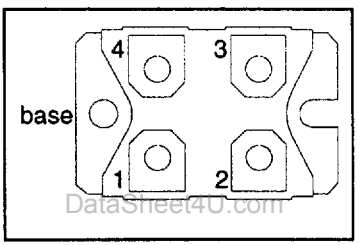
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BUK416	-100AE	-100BE	
V_{DS}	Drain-source voltage	100	100	V
I_D	Drain current (DC)	110	100	A
P_{tot}	Total power dissipation	310	310	W
$R_{DS(ON)}$	Drain-source on-state resistance	13.0	16.0	mΩ

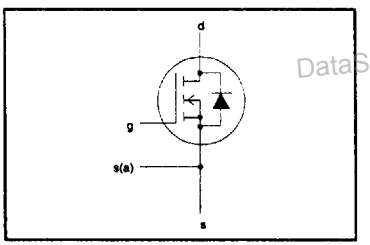
PINNING - SOT227B

PIN	DESCRIPTION
1	source
2	gate
3	drain
4	ancillary source
base	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DS}	Drain-source voltage	-	-	100		V
V_{DGR}	Drain-gate voltage	R_{GS} = 20 kΩ	-	100		V
$\pm V_{GS}$	Gate-source voltage	-	-	30		V
				-100AE	-100BE	
I_D	Drain current (DC)	T_{mb} = 25 °C	-	110	100	A
I_D	Drain current (DC)	T_{mb} = 100 °C	-	70	60	A
I_{DM}	Drain current (pulse peak value)	T_{mb} = 25 °C	-	440	400	A
$I_{S(A)M}$	Ancillary Source current (pulse peak value)		-	5.0		A
P_{tot}	Total power dissipation	T_{mb} = 25 °C	-	310		W
T_{stg}	Storage temperature	-	- 40	150		°C
T_j	Junction Temperature	-	-	150		°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance. junction to mounting base		-	-	0.4	K/W
$R_{th\ mb\text{-}hs}$	Thermal resistance. mounting base to heatsink	with heatsink compound	-	0.05	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 1.0 mA	100	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	5	50	µA
I_{DSS}	Zero gate voltage drain current	V_{DS} = 100 V; V_{GS} = 0 V; T_j =125 °C	-	0.5	5.0	mA
I_{GSS}	Gate source leakage current	V_{GS} = ±30 V; V_{DS} = 0 V	-	10	200	nA
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; **BUK416-100AE**	-	11.0	13.0	mΩ
		I_D = 55 A **BUK416-100BE**	-	14.0	16.0	mΩ

DYNAMIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 10 V; I_D = 55 A	50.0	70.0	-	S
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	7.5	10.0	nF
C_{oss}	Output capacitance		-	2.3	3.0	nF
C_{rss}	Feedback capacitance		-	0.65	1.0	nF
$t_{d\,on}$	Turn-on delay time	V_{DD} = 30 V; I_D = 3 A;	-	100	150	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_{GS} = 50 Ω;	-	150	250	ns
$t_{d\,off}$	Turn-off delay time	R_{gen} = 50 Ω	-	750	1000	ns
t_f	Turn-off fall time	Resistive Load	-	250	350	ns
$t_{d\,on}$	Turn-on delay time	V_{DD} = 50 V; I_D = 110 A;	-	40	80	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_{gen} = 3.3 Ω	-	200	300	ns
$t_{d\,off}$	Turn-off delay time	Resistive Load	-	150	200	ns
t_f	Turn-off fall time		-	70	100	ns
L_d	Internal drain inductance	Measured from contact screw on terminal 3 to centre of die	-	5	-	nH
L_s	Internal source inductance	Measured from contact screw on terminal 1 to source bond pad	-	5	-	nH

ISOLATION

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	R.M.S. voltage from terminals to mounting base	Sinusoidal voltage waveform; f = 50 - 60 Hz	-	-	2500	V
C_{isol}	Capacitance from T3 to mounting base	f = 1 MHz	-	45	-	pF

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	110	A
I_{DRM}	Pulsed reverse drain current	-	-	-	440	A
V_{SD}	Diode forward voltage	I_F = 110 A ;V_{GS} = 0 V	-	1.1	1.7	V
t_{rr}	Reverse recovery time	I_F = 110A; -dI_F/dt = 100 A/µs;	-	500	-	ns
Q_{rr}	Reverse recovery charge	V_{GS} = 0 V; V_R = 30 V	-	10	-	µC

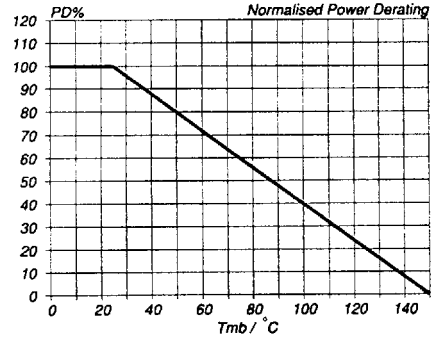


Fig.1. Normalised power dissipation.
$PD\% = 100 \cdot P_D / P_{D\,25\,°C} = f(T_{mb})$

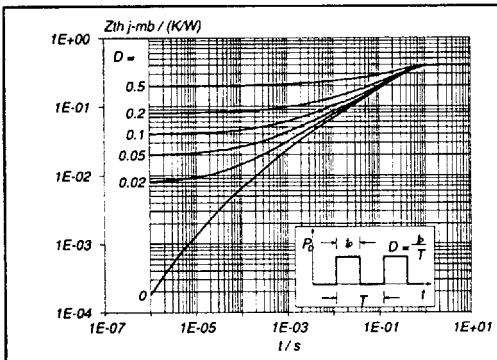


Fig.4. Transient thermal impedance.
$Z_{th\,j\text{-}mb} = f(t)$; parameter $D = t_p/T$

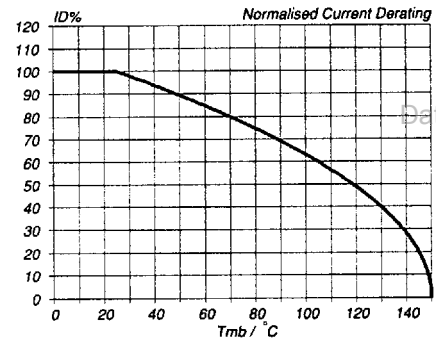


Fig.2. Normalised continuous drain current.
$ID\% = 100 \cdot I_D / I_{D\,25\,°C} = f(T_{mb})$; conditions: $V_{GS} \geq 10$ V

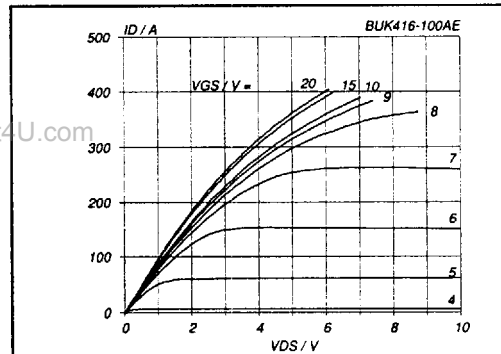


Fig.5. Typical output characteristics, $T_j = 25$ °C.
$I_D = f(V_{DS})$; parameter V_{GS}

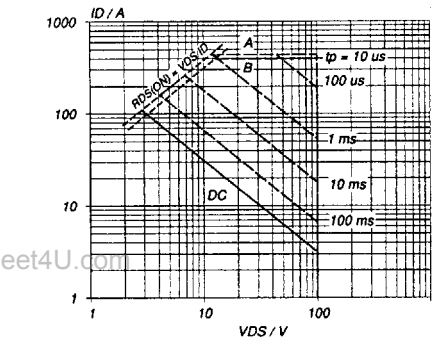


Fig.3. Safe operating area. $T_{mb} = 25$ °C
I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

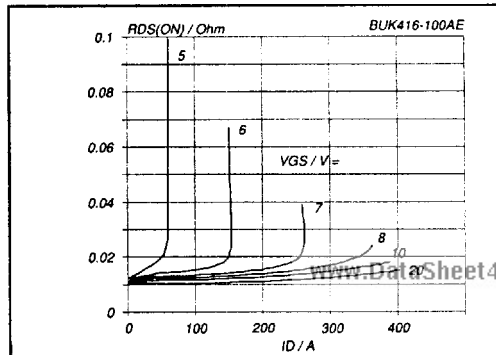


Fig.6. Typical on-state resistance, $T_j = 25$ °C.
$R_{DS(ON)} = f(I_D)$; parameter V_{GS}

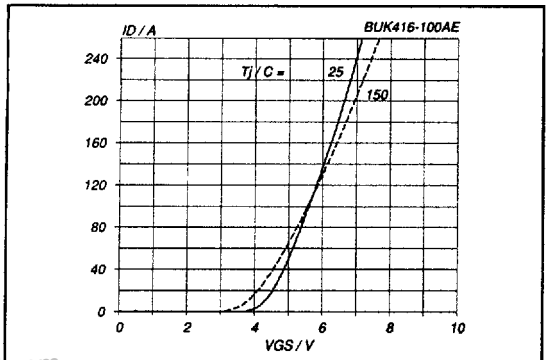


Fig.7. Typical transfer characteristics.
$I_D = f(V_{GS})$; conditions: V_{DS} = 10 V; parameter T_j

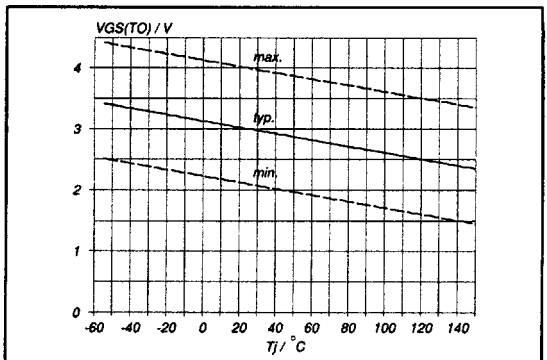


Fig.10. Gate threshold voltage.
$V_{GS(TO)} = f(T_j)$; conditions: I_D = 1 mA; $V_{DS} = V_{GS}$

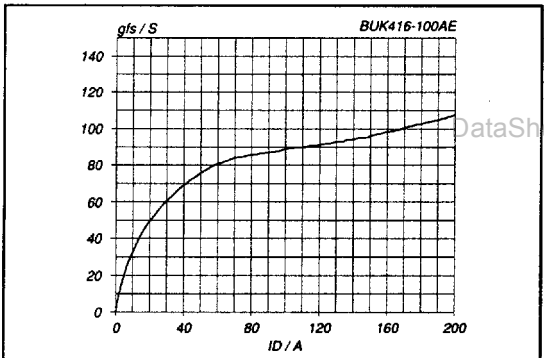


Fig.8. Typical transconductance, T_j = 25 °C.
$g_{fs} = f(I_D)$; conditions: V_{DS} = 10 V

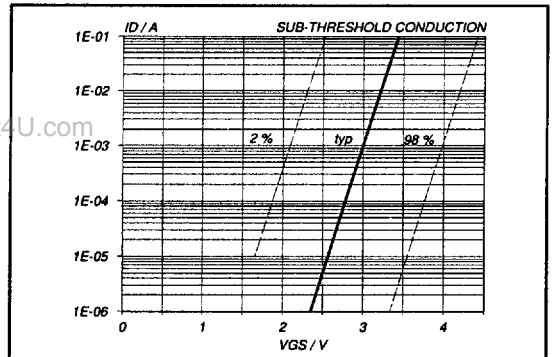


Fig.11. Sub-threshold drain current.
$I_D = f(V_{GS})$; conditions: T_j = 25 °C; $V_{DS} = V_{GS}$

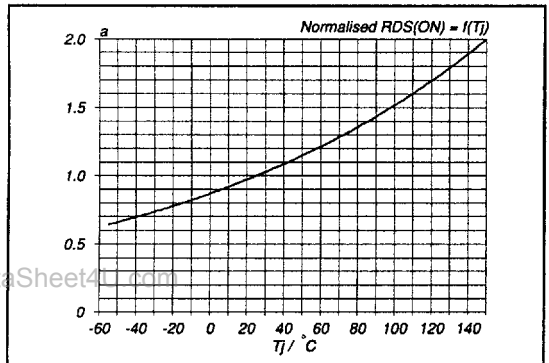


Fig.9. Normalised drain-source on-state resistance.
$a = R_{DS(ON)}/R_{DS(ON)25\,°C} = f(T_j)$; I_D = 55 A; V_{GS} = 10 V

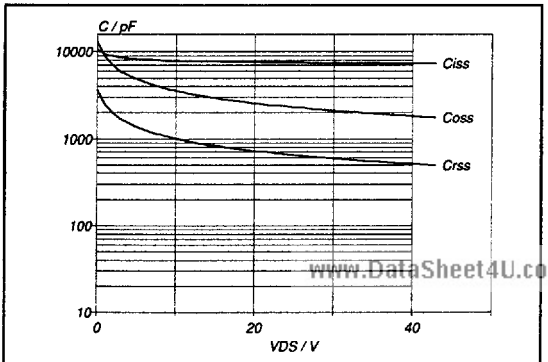


Fig.12. Typical capacitances, C_{iss}, C_{oss}, C_{rss}.
$C = f(V_{DS})$; conditions: V_{GS} = 0 V; f = 1 MHz

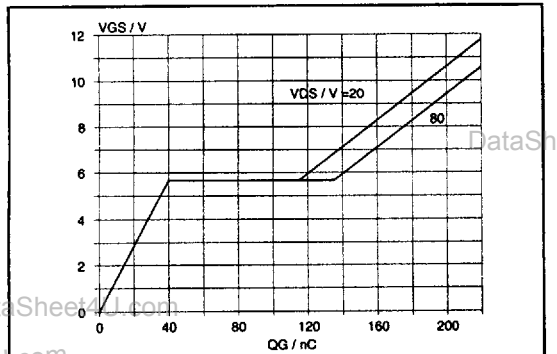


Fig.13. Typical turn-on gate-charge characteristics. $V_{GS} = f(Q_G)$; conditions: $I_D = 110$ A; parameter V_{DS}

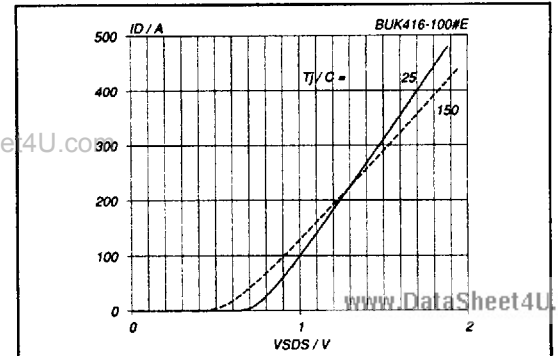


Fig.14. Typical reverse diode current. $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0$ V; parameter T_j